# BLM8D1822S-50PB; BLM8D1822S-50PBG

Rev. 3 — 23 November 2017

#### **Product profile** 1.

### 1.1 General description

The BLM8D1822S-50PB(G) is a dual section, 2-stage fully integrated Doherty MMIC solution using Ampleon's state of the art GEN8 LDMOS technology. The carrier and peaking device, input splitter and output combiner are integrated in a single package. This multiband device is perfectly suited as general purpose driver or small cell final in the frequency range from 1805 MHz to 2170 MHz. Available in gull wing or flat lead outline.

#### Table 1. Performance

Typical RF performance at  $T_{case}$  = 25 °C;  $I_{Da}$  = 104 mA (carrier);  $V_{GSa(ceaking)}$  =  $V_{GSa(carrier)} - 0.65$  V. Test signal: 3GPP test model 1; 64 DPCH; PAR = 9.9 dB at 0.01% probability on CCDF; per section.

Test signal	f	V <sub>DS</sub>	P <sub>L(AV)</sub>	G <sub>p</sub>	ησ	ACPR <sub>5M</sub>
	(MHz)	(V)	(W)	(dB)	(%)	(dBc)
single carrier W-CDMA	2167.5	28	5	26.5	37	-34

### 1.2 Features and benefits

- Integrated input splitter
- Integrated output combiner
- High efficiency
- Designed for broadband operation (frequency 1805 MHz to 2170 MHz)
- High section-to-section isolation enabling multiple combinations
- Integrated temperature compensated bias
- Independent control of carrier and peaking bias
- Integrated ESD protection
- Excellent thermal stability
- Source impedance 50 Ω; high power gain
- Compliant to Directive 2002/95/EC, regarding restriction of hazardous substances (RoHS)

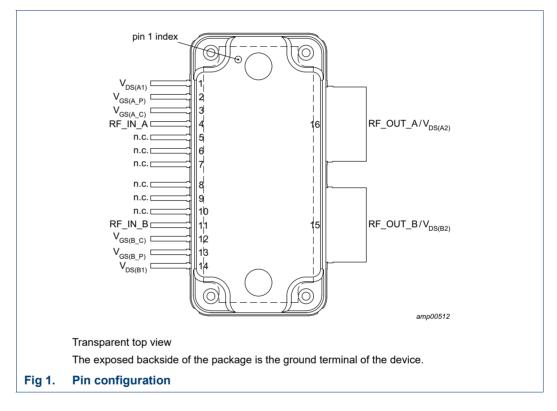
### LDMOS 2-stage integrated Doherty MMIC

### 1.3 Applications

- RF power MMIC for multi-carrier and multi-standard GSM, W-CDMA and LTE base stations in the 1805 MHz to 2170 MHz frequency range. Possible circuit topologies are the following as also depicted in <u>Section 8.1</u>:
  - Dual section or single ended
  - Quadrature combined
  - Push-pull

### 2. Pinning information

### 2.1 Pinning



### 2.2 Pin description

Table 2. Pin d	lescription	
Symbol	Pin	Description
V <sub>DS(A1)</sub>	1	drain-source voltage of driver stages of section A
V <sub>GS(A_P)</sub>	2	gate-source voltage of peaking A_P
V <sub>GS(A_C)</sub>	3	gate-source voltage of carrier A_C
RF_IN_A	4	RF input section A
n.c.	5	not connected
n.c.	6	not connected
n.c.	7	not connected

#### BLM8D1822S-50PB\_S-50PBG

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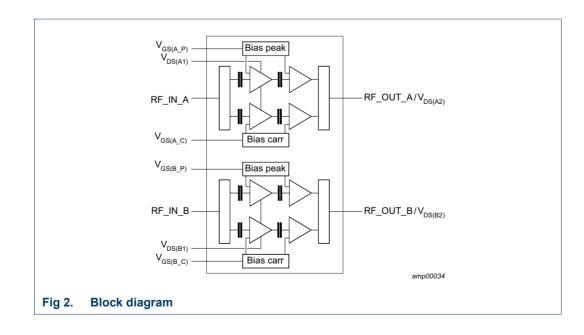
Table 2. Pin descr	ription	continued
Symbol	Pin	Description
n.c.	8	not connected
n.c.	9	not connected
n.c.	10	not connected
RF_IN_B	11	RF input section B
V <sub>GS(B_C)</sub>	12	gate-source voltage of carrier B_C
V <sub>GS(B_P)</sub>	13	gate-source voltage of peaking B_P
V <sub>DS(B1)</sub>	14	drain-source voltage of driver stages of section B
RF_OUT_B/V <sub>DS(B2)</sub>	15	RF output section B / drain-source voltage of final stages of section B
RF_OUT_A/V <sub>DS(A2)</sub>	16	RF output section A / drain-source voltage of final stages of section A
GND	flange	RF ground

# 3. Ordering information

### Table 3.Ordering information

Type number	Packag	je	
	Name	Description	Version
BLM8D1822S-50PB	-	plastic, heatsink small outline package; 16 leads (flat)	SOT1211-3
BLM8D1822S-50PBG	-	plastic, heatsink small outline package; 16 leads	SOT1212-3

# 4. Block diagram



LDMOS 2-stage integrated Doherty MMIC

### 5. Limiting values

#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

1				I	
Symbol	Parameter	Conditions	Min	Мах	Unit
V <sub>DS</sub>	drain-source voltage		-	65	V
V <sub>GS</sub>	gate-source voltage		-0.5	+13	V
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature	[1]	-	225	°C
T <sub>case</sub>	case temperature		-	150	°C

[1] Continuous use at maximum temperature will affect the reliability. For details refer to the online MTF calculator.

### 6. Thermal characteristics

#### Table 5. Thermal characteristics

Measured	for total device.			
Symbol	Parameter	Conditions	Value	Unit
R <sub>th(j-c)</sub>	thermal resistance from junction to case	$T_{case} = 90 \ ^{\circ}C; P_{L} = 10 \ W$ [1]	1.06	K/W
		$T_{case} = 90 ^{\circ}C; P_{L} = 20 ^{\circ}W$	0.86	K/W

[1] When operated with a 1-carrier W-CDMA with PAR = 8 dB.

# 7. Characteristics

#### Table 6. DC characteristics

 $T_{case}$  = 25 °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Carrier		1				
V <sub>GSq</sub>	gate-source quiescent voltage	V <sub>DS</sub> = 28 V; I <sub>D</sub> = 104 mA	1.6	2.1	2.5	V
I <sub>DSX</sub>	drain cut-off current	V <sub>GS</sub> = 5.65 V; V <sub>DS</sub> = 10 V	l -	2.60	-	А
		V <sub>GS</sub> = 5.65 V; V <sub>DS</sub> = 10 V	l -	0.52	-	А
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 1 V; V <sub>DS</sub> = 0 V	-	-	140	nA
Peaking	1		1	1	1	
I <sub>DSX</sub>	drain cut-off current	V <sub>GS</sub> = 5.65 V; V <sub>DS</sub> = 10 V [1	l -	2.74	-	А
		V <sub>GS</sub> = 5.65 V; V <sub>DS</sub> = 10 V	l -	0.57	-	А
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 1 V; V <sub>DS</sub> = 0 V	-	-	140	nA
Final sta	ges					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	V <sub>GS</sub> = 0 V; I <sub>D</sub> = 300 mA	65	-	-	V
I <sub>DSS</sub>	drain leakage current	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 28 V	-	-	1.4	μA
Driver st	ages					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	V <sub>GS</sub> = 0 V; I <sub>D</sub> = 60 mA	65	-	-	V
I <sub>DSS</sub>	drain leakage current	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 28 V	-	-	1.4	μA

- [1] Final stage.
- [2] Driver stage.

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#### Table 7. RF Characteristics

Typical RF performance at  $T_{case} = 25 \ ^{\circ}C$ ;  $V_{DS} = 28 \ V$ ;  $I_{Dq} = 104 \ mA$  (carrier);  $V_{GSq(peaking)} = V_{GSq(carrier)} - 0.65 \ V$ ;  $P_{L(AV)} = 5 \ W$ . Unless otherwise specified, measured in an Ampleon straight lead production circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Test sign	al: single carrier W-CDMA [1]					
G <sub>p</sub>	power gain	f = 1807.5 MHz	-	26	-	dB
		f = 2167.5 MHz	24.5	26.5	28.5	dB
η <sub>D</sub>	drain efficiency	f = 2167.5 MHz	31	37	-	%
RL <sub>in</sub>	input return loss	f = 2167.5 MHz	-	-19	-10	dB
ACPR <sub>5M</sub>	adjacent channel power ratio (5 MHz)	f = 2167.5 MHz	-	-34	-26	dBc
PAR <sub>O</sub>	output peak-to-average ratio	f = 2167.5 MHz	6.7	7.8	-	dB

[1] 3GPP test model 1; 64 DPCH; PAR = 9.9 dB at 0.01% probability on CCDF.

# 8. Application information

#### Table 8.Typical performance

 $T_{case} = 25 \, \circ C$ ;  $V_{DS} = 28 \, V$ ;  $I_{Dq} = 190 \, mA$  (carrier and peaking). Test signal: 1-carrier W-CDMA; test model 1; 64 DPCH; PAR = 9.9 dB at 0.01 % probability CCDF; unless otherwise specified, measured in an Ampleon f = 1805 MHz to 2170 MHz combined integrated Doherty application circuit (see <u>Figure 3</u> for the component layout and <u>Figure 4</u> for the electrical schematic).

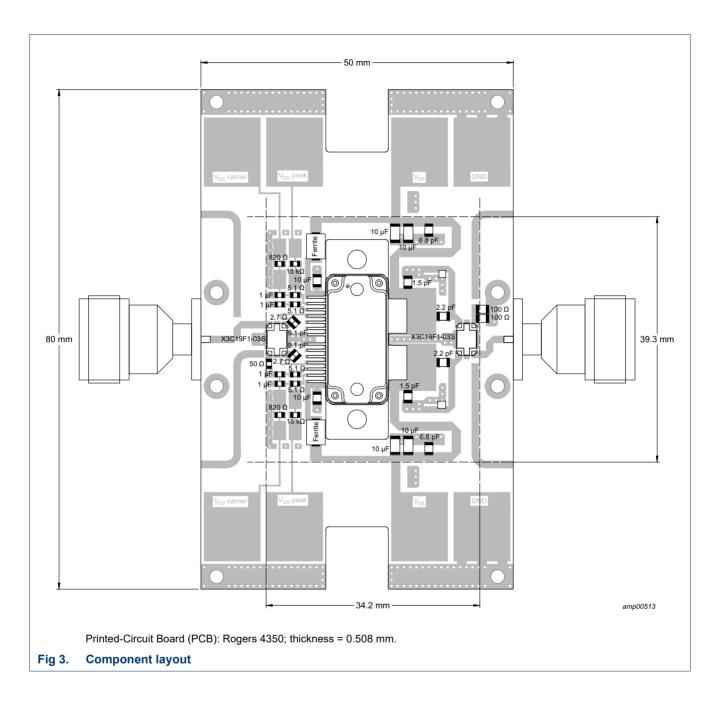
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
P <sub>L(1dB)</sub>	output power at 1 dB gain compression	f = 1960 MHz	[1]	-	48.4	-	dBm
$\phi_{s21}/\phi_{s21}(norm)$	normalized phase response	at 3 db compression point; f = 1960 MHz	[1]	-	-0.4	-	0
$\eta_D$	drain efficiency	8 db OBO (P <sub>L</sub> = 40.4 dBm); f = 1960 MHz		-	38.9	-	%
G <sub>p</sub>	power gain	P <sub>L(AV)</sub> = 40.4 dBm; f = 1960 MHz		-	25	-	dB
B <sub>video</sub>	video bandwidth	P <sub>L(AV)</sub> set to obtain IMD3 = -30 dBc; 2-tone CW; f = 1960 MHz		-	185	-	MHz
G <sub>flat</sub>	gain flatness	P <sub>L(AV)</sub> = 40.4 dBm; f = 1805 MHz to 2170 MHz		-	1	-	dB
ACPR <sub>5M</sub>	adjacent channel power ratio (5M)	P <sub>L(AV)</sub> = 40.4 dBm; f = 1960 MHz		-	-38.2	-	dB
$\Delta G / \Delta T$	gain variation with temperature	f = 2140 MHz		-	0.04	-	dB/∘C
s <sub>12</sub>   <sup>2</sup>	isolation	between sections A and B; $P_{L(AV)} = 15.2 \text{ dBm}$ ; f = 2140 MHz; measured on dual section evaluation board		-	24	-	dB
К	Rollett stability factor	$T_{case} = -40 \text{ °C}; f = 0.3 \text{ GHz to}$ 3 GHz	[2]	-	>3	-	

[1] 25 ms CW power sweep measurement.

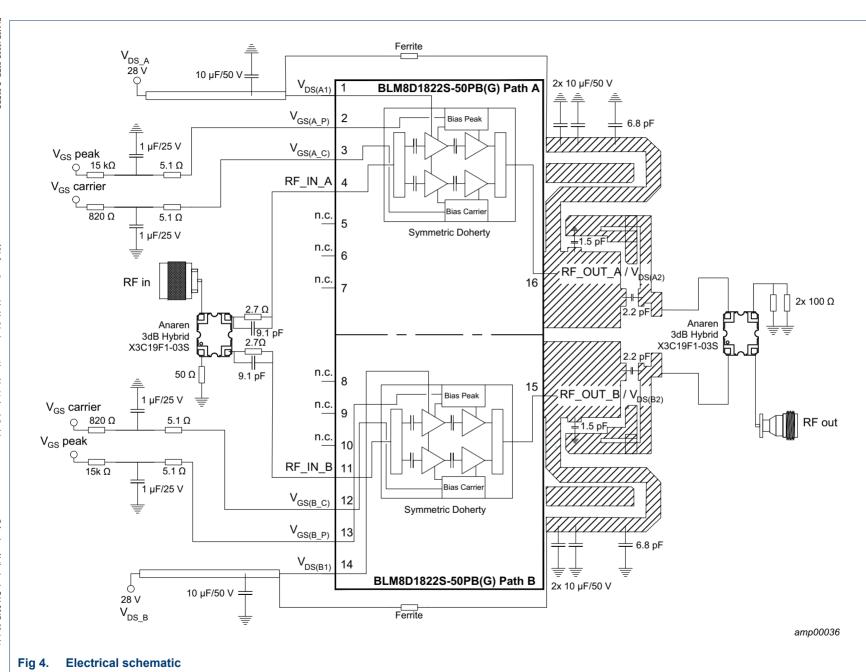
[2] For both sections (S-parameters measured with load pull jig).

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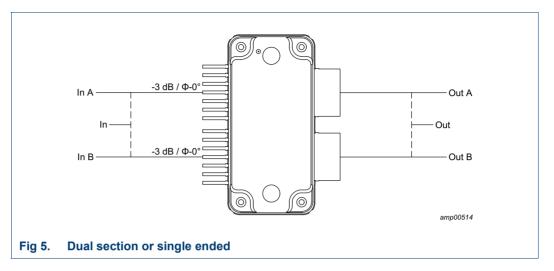


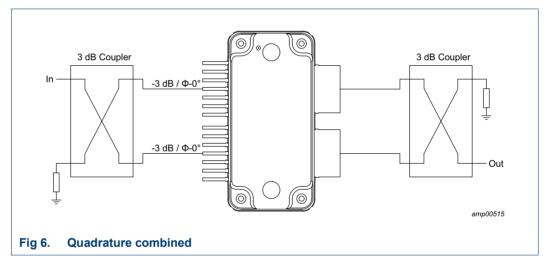


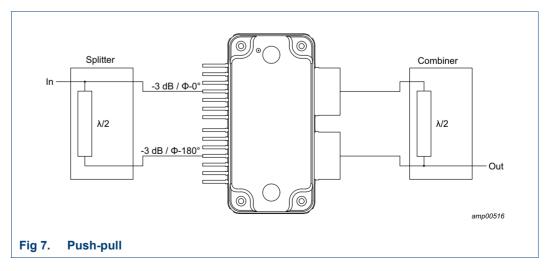
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### 8.1 Possible circuit topologies







#### LDMOS 2-stage integrated Doherty MMIC

### 8.2 Ruggedness in a Doherty operation

The BLM8D1822S-50PB and BLM8D1822S-50PBG are capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions:  $V_{DS}$  = 32 V;  $I_{Dq}$  = 104 mA (carrier);  $V_{GSq(peaking)}$  =  $V_{GSq(carrier)}$  – 0.65 V;  $P_i$  corresponding to  $P_{L(3dB)}$  under  $Z_S$  = 50  $\Omega$  load; f = 2140 MHz (CW);  $T_{case}$  = 25 °C per section unless otherwise specified

### 8.3 Impedance information

#### Table 9. Typical impedance for optimum Doherty operation

Measured load-pull data per section; test signal: pulsed CW;  $T_{case} = 25 \text{ °C}$ ;  $V_{DS} = 28 \text{ V}$ ;  $I_{Dq} = 104 \text{ mA}$  (carrier);  $V_{GSq(peaking)} = V_{GSq(carrier)} - 0.65 \text{ V}$ ;  $t_p = 100 \mu$ s;  $\delta = 10 \%$ . Typical values per section unless otherwise specified.

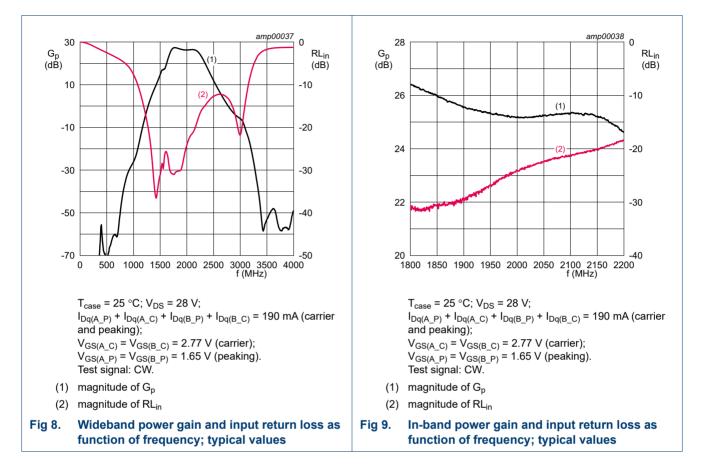
	tuned for optimu	m Doherty opera	tion		
f	ZL	G <sub>p(max)</sub>	PL	໗ <mark>add </mark> [1]	໗ <sub>add</sub> [2]
(MHz)	(Ω)	(dB)	(dBm)	(%)	(%)
BLM8D18	22S-50PB			·	
1700	4.20 – j2.10	27.1	45.2	46.1	39.0
1800	4.00 – j2.90	28.6	45.2	48.8	41.4
1900	3.85 – j3.90	27.6	45.2	47.1	42.1
2000	4.90 – j5.50	27.5	45.2	49.4	43.2
2100	5.40 – j5.70	27.5	45.2	53.5	41.9
2200	8.00 – j5.20	27.1	45.2	55.3	40.6
2300	9.10 – j4.70	25.6	45.2	53.8	37.4
BLM8D18	22S-50PBG		I		
1700	4.20 - j3.90	27.8	45.2	43.3	37.8
1800	4.10 – j4.50	28.1	45.2	45.4	39.7
1900	3.90 – j6.00	27.6	45.2	45.4	40.8
2000	4.60 – j7.80	27.3	45.2	45.2	40.1
2100	5.40 – j8.40	27.7	45.3	50.1	52.0
2200	8.20 – j8.50	27.5	45.2	53.0	38.6
2300	9.50 – j7.50	26.2	45.2	54.7	36.2

[1] at 45 dBm (nearly 3 dB compression point).

[2] at 37 dBm (nearly 8 dB OBO point).

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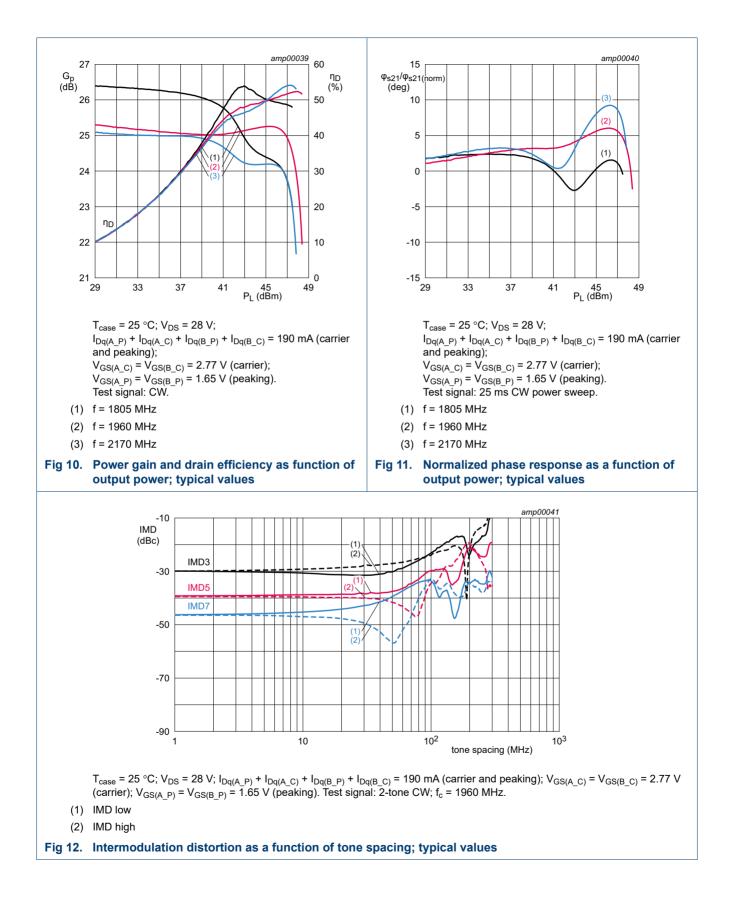
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8.4 Graphs

# BLM8D1822S-50PB(G)

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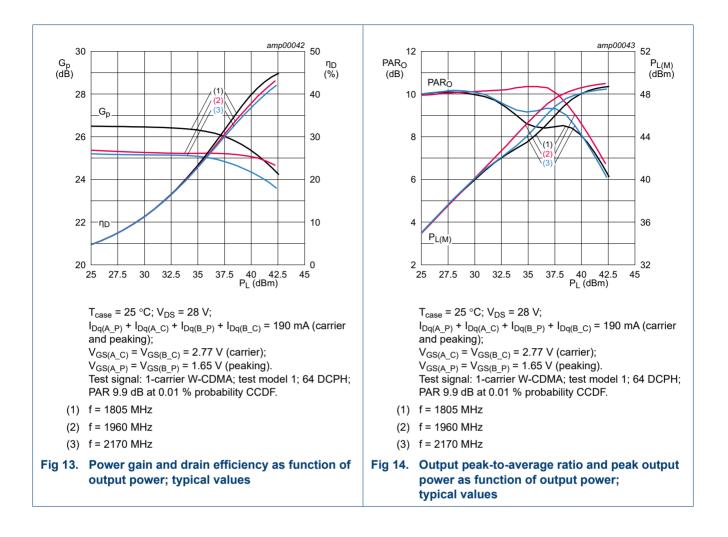


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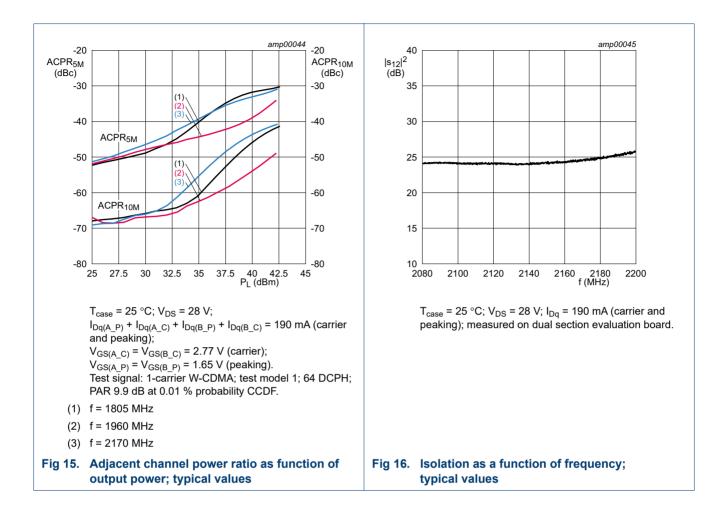
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#### LDMOS 2-stage integrated Doherty MMIC

### 9. Package outline

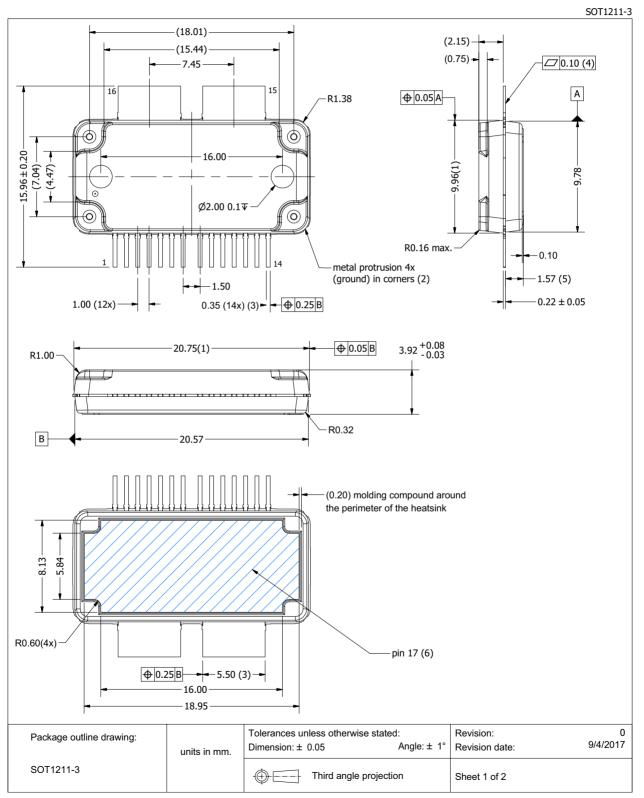


Fig 17. Package outline SOT1211-3 (sheet 1 of 2)

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SOT1211-3

(1)		on. Areas located adjacent to the leads have a	maximum mold protrusion of 0.25
(1)	mm (per side) and 0.62 mm max. in len		
		gth. In between the 14 leads the protrusion is 0.	25 mm. max. At all other areas the
	mold protrusion is maximum 0.15 mm p	er side. See also detail B.	
(2)	The metal protrusion (tie bars) in the co	rner will not stick out of the molding compound	protrusions (detail A).
(3)	The lead dambar (metal) protrusions ar	e not included. Add 0.14 mm max to the total le	ad dimension at the dambar location
(4)	The lead coplanarity over all leads is 0.	1 mm maximum.	
(5)	Dimension is measured 0.5 mm from th	e edge of the top package body.	
(6)	The hatched area indicates the exposed	d metal heatsink.	
(7)	The leads and exposed heatsink are pla	ated with matte Tin (Sn).	
	B	A lead dambar location	0.25 mox.(1) 0.25 mox.(1) 0.25 mox.(1) 0.25 mox.(1) 0.25 mox.(1) 0.25 mox.(1)
		DETAIL B SCALE 50:1	

#### Fig 18. Package outline SOT1211-3 (sheet 2 of 2)

BLM8D1822S-50PB\_S-50PBG

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**Product data sheet** 

#### LDMOS 2-stage integrated Doherty MMIC

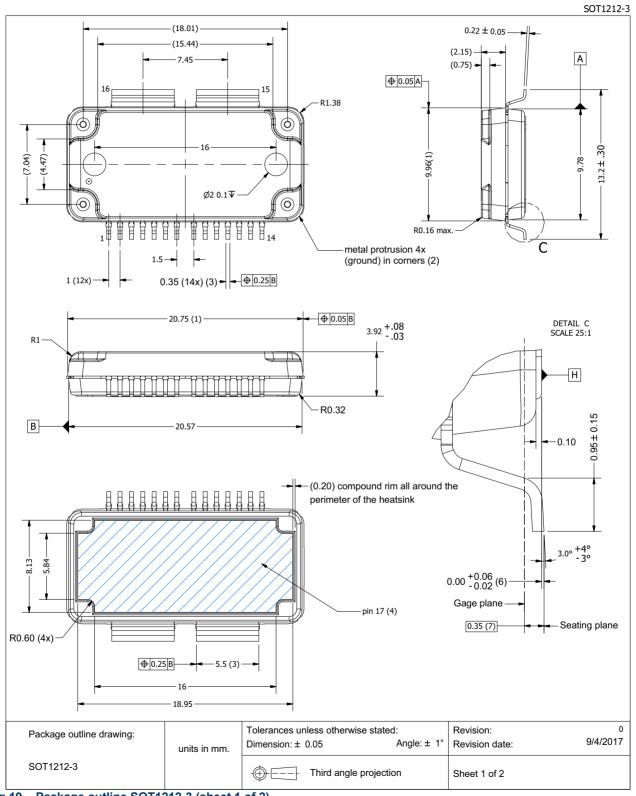


Fig 19. Package outline SOT1212-3 (sheet 1 of 2)

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SOT1212-3

Items			Description	
	Dimensions are exc	cluding mold protru	usion. Areas located adjacent to the leads have a maximum mold protrusion of 0	.25
(1)	mm (per side) and (	0.62 mm max. in le	ength. In between the 14 leads the protrusion is 0.25 mm max. At all other areas	the
	mold protrusion is n	naximum 0.15 mm	n per side. See also detail B.	
(2)	The metal protrusio	n (tie bars) in the o	corner will not stick out of the molding compound protrusions (detail A).	
(3)	The lead dambar (n	netal) protrusions a	are not included. Add 0.14 mm max to the total lead dimension at the dambar loc	ation.
(4)	The hatched area ir	ndicated the expos	sed heatsink.	
(5)	The leads and expo	osed heatsink are p	plated with matte Tin (Sn).	
(6)	Dimension is measured heatsink is higher the		to the bottom of the heatsink Datum H. Positive value means that the bottom of the lead.	ne
(7)	Gage plane (foot le	ngth) to be measu	ured from the seating plane.	
(				
(		B	DETAIL A SCALE 25:1	
(		B		
		B	SCALE 25:1	
		B	SCALE 25:1	
( Package of	utline drawing:	B D D D D D D D D D D D D D D D D D D D	SCALE 25:1	9/4/2

### Fig 20. Package outline SOT1212-3 (sheet 2 of 2)

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#### LDMOS 2-stage integrated Doherty MMIC

# **10. Handling information**

#### CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

#### Table 10. ESD sensitivity

ESD model	Class
Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002	C2 [1]
Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001	1C 🛛

 CDM classification C2 is granted to any part that passes after exposure to an ESD pulse of 500 V, but fails after exposure to an ESD pulse of 1000 V.

[2] HBM classification 1C is granted to any part that passes after exposure to an ESD pulse of 1000 V, but fails after exposure to an ESD pulse of 2000 V.

### 11. Abbreviations

#### Table 11.Abbreviations

Aaronym	Description
Acronym	Description
3GPP	3rd Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
DPCH	Dedicated Physical CHannel
ESD	ElectroStatic Discharge
GEN8	Eighth Generation
GSM	Global System for Mobile Communications
LDMOS	Laterally Diffused Metal Oxide Semiconductor
LTE	Long Term Evolution
MMIC	Monolithic Microwave Integrated Circuit
MTF	Median Time to Failure
OBO	Output Back Off
PAR	Peak-to-Average Ratio
VSWR	Voltage Standing-Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

LDMOS 2-stage integrated Doherty MMIC

# 12. Revision history

### Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BLM8D1822S-50PB_S-50PBG v.3	20171123	Product data sheet	-	BLM8D1822S-50PB_ S-50PBG v.2	
Modifications:	<ul> <li>Figure 1 on page 2: pin 1 index position aligned</li> <li>Figure 3 on page 6: pin 1 index position aligned</li> <li>Figure 5 on page 8: pin 1 index position aligned</li> <li>Figure 6 on page 8: pin 1 index position aligned</li> <li>Figure 7 on page 8: pin 1 index position aligned</li> </ul>				
BLM8D1822S-50PB_S-50PBG v.2	20171117	Product data sheet	-	BLM8D1822S-50PB_ S-50PBG v.1	
BLM8D1822S-50PB_S-50PBG v.1	20160322	Product data sheet	-	-	

# 13. Legal information

### 13.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

- [2] The term 'short data sheet' is explained in section "Definitions".
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.ampleon.com.

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